

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	26	430/22,30,311,313,322,330.ccls. and (((contribut\$6 near3 degree or proportion or coefficient\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4))))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:08
L2	2178	(430/22,30,311,313,322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)) not (430/22,30,311,313,322,330.ccls. and (((contribut\$6 near3 degree or proportion or coefficient\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4)))))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:08
L3	843	(430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:10

L4	5	427/8-10 not (430/22,30,311,313, 322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)) not (430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:11
L5	100	(substrate or wafer) near3 (defect or fault) same (nozzle or pipe or spread\$3 or flow\$3 or dispens\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:14
L6	20	427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) near3 (accelerat\$3 or decelerat\$3 or position\$3 or location)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:17
L7	14	427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) same (accelerat\$3 or decelerat\$3 or position\$3 or location) not (427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) near3 (accelerat\$3 or decelerat\$3 or position\$3 or location))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:18
L8	10	(427/8-10 or 438/5-18).ccls. and ((contribut\$6 near3 degree or proportion or coefficient\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4)))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:19

L9	21	(427/8-10 or 438/5-18).ccls. and (formula\$1 or equation) same (resist or photoresist) same thick\$4 not ((contribut\$6 near3 degree or proportion or coefficient\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4)))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:19
L10	64	(430/22,30 or 438/5-18).ccls. and (etch\$3 near3 (line or pattern) same (alarm\$3 or alert\$3 or warn\$3 or buzz\$3 or signal\$4 or notif\$4))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:20
L12	92	semiconduct\$3 and (etch\$3 same (alarm\$3 or alert\$3 or warn\$3 or buzz\$3 or notif\$4) same (operator or human\$3 or manual\$3 or person\$6 or eye\$3))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:20
L13	64	(430/22,30 or 438/5-18).ccls. and (etch\$3 near3 (line or pattern) same (alarm\$3 or alert\$3 or warn\$3 or buzz\$3 or signal\$4 or notif\$4))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:21
L14	21	(427/8-10 or 438/5-18).ccls. and (formula\$1 or equation) same (resist or photoresist) same thick\$4 not ((contribut\$6 near3 degree or proportion or coefficient\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4)))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:22
L15	10	(427/8-10 or 438/5-18).ccls. and ((contribut\$6 near3 degree or proportion or coefficient\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4)))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:22

L16	14	427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) same (accelerat\$3 or decelerat\$3 or position\$3 or location) not (427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) near\$3 (accelerat\$3 or decelerat\$3 or position\$3 or location))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:22
L17	20	427/8-10.ccls. and (resist or photoresist) same (nozzle or dispens\$3 or spread\$3 or pip\$3 or eject\$3) near\$3 (accelerat\$3 or decelerat\$3 or position\$3 or location)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:23
L18	100	(substrate or wafer) near\$3 (defect or fault) same (nozzle or pipe or spread\$3 or flow\$3 or dispens\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:23
L19	5	427/8-10 not (430/22,30,311,313, 322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)) not (430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:35
L20	843	(430/22,30.ccls. not (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:25

L21	2178	(430/22,30,311,313,322,330.ccls. and (((spin\$4 or rotat\$3 or centrifug\$6) and (expos\$3 or radiat\$3 or irradiat\$3 or light\$3) and develop\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7))) and ((etch\$3 or heat\$3 or bak\$3 or prebak\$3 or postbak\$3) same (resist or photoresist or photosens\$5 or photopolymer\$7)) not (430/22,30, 311,313,322,330.ccls. and ((contribut\$6 near3 degree or proportion or coefficient\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4)))))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:25
L22	26	430/22,30,311,313,322,330.ccls. and ((contribut\$6 near3 degree or proportion or coefficient\$3 or factor\$3 or amount\$3 or percent\$3 or relativ\$3 or grad\$3 or level\$3 or exten\$4) same (resist or photoresist) same (thick\$4 and temperature and pressure and (humidi\$5 or moistur\$6 or wet\$4))))	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	ON	2004/11/19 10:25
L23	1	("6130750").PN.	US-PGPUB; USPAT; EPO; JPO; IBM_TDB	OR	OFF	2004/11/19 10:35